

PNP SILICON DUAL TRANSISTOR

Qualified per MIL-PRF-19500/336

Devices

2N3810	2N3811
2N3810L	2N3811L
2N3810U	2N3811U

Qualified Level

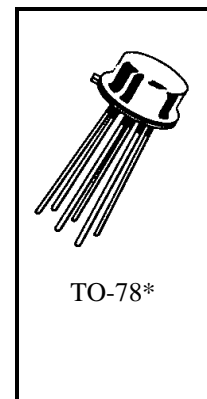
JAN
JANTX
JANTXV

MAXIMUM RATINGS

Ratings	Symbol	Value	Unit	
Collector-Emitter Voltage	V_{CEO}	60	Vdc	
Collector-Base Voltage	V_{CBO}	60	Vdc	
Emitter-Base Voltage	V_{EBO}	5.0	Vdc	
Collector Current	I_C	50	mAdc	
		One Section¹	Both Sections²	
Total Power Dissipation @ $T_A = +25^{\circ}\text{C}$	P_T	0.5	0.6	W
Operating & Storage Junction Temperature Range	T_J, T_{stg}	-65 to +200		$^{\circ}\text{C}$

1) Derate linearly 2.86 mW/ $^{\circ}\text{C}$ for $T_A > +25^{\circ}\text{C}$

2) Derate linearly 3.43 mW/ $^{\circ}\text{C}$ for $T_A > +25^{\circ}\text{C}$



*See appendix A for package outline

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}\text{C}$ unless otherwise noted)

Characteristics	Symbol	Min.	Max.	Unit
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OFF CHARACTERISTICS

Collector-Base Breakdown Voltage $I_C = 10 \mu\text{Adc}$	$V_{(BR)CBO}$	60		Vdc
Collector-Emitter Breakdown Current $I_C = 10 \text{mAdc}$	$V_{(BR)CEO}$	60		Vdc
Emitter-Base Breakdown Voltage $I_E = 10 \mu\text{Adc}$	$V_{(BR)EBO}$	5.0		Vdc
Collector-Base Cutoff Current $V_{CB} = 50 \text{Vdc}$	I_{CBO}		10	ηAdc
Emitter-Base Cutoff Current $V_{EB} = 4.0 \text{Vdc}$	I_{EBO}		10	ηAdc

